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KA1M0565R/KA1H0565R

Fairchild Power Switch(FPS)

Features

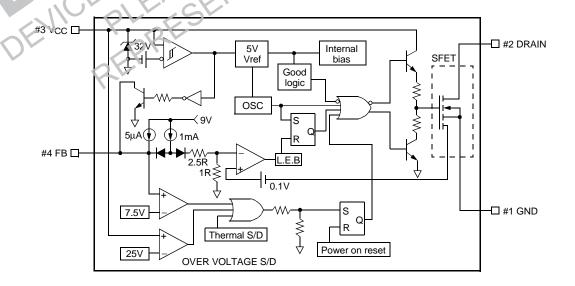
- Precision fixed operating frequency
- KA1M0565R (67KHz),KA1H0565R (100KHz)
- Pulse by pulse over current limiting
- · Over load protection
- Over voltage protection (Min. 23V)
- Internal thermal shutdown function
- Under voltage lockout
- Internal high voltage sense FET
- · Auto restart

Description

The Fairchild Power Switch(FPS) product family is specially designed for an off-line SMPS with minimal external components. The Fairchild Power Switch(FPS) consist of high voltage power SenseFET and current mode PWM controller IC. PWM controller features integrated fixed oscillator, under voltage lock out, leading edge blanking, optimized gate turn-on/turn-off driver, thermal shut down protection, over voltage protection, temperature compensated precision current sources for loop compensation and fault protection circuit, compared to discrete MOSFET and controller or RCC switching converter solution, a Fairchild Power Switch(FPS) can reduce total component count, design size, weight and at the same time increase & efficiency productivity, and system reliability. It has a basic platform well suited for cost effective design in either a flyback converter or a for ward converter.



Internal Block Diagram



Absolute Maximum Ratings

Maximum Drain voltage (1) Drain Gate voltage (R _G S=1MΩ) Gate-source (GND) voltage Drain current pulsed (2) Single pulsed avalanche energy (3) Continuous drain current (T _C =25°C) Continuous drain current (T _C =100°C) Maximum Supply voltage Input voltage range Total power dissipation Operating ambient temperature Storage temperature Notes: 1. Tj=25°C to 150°C 2. Repetitive rating: Pulse width limited by maximur 3. L=30mH, V _{DD} =50V, R _G = 27Ω, starting Tj=25°C	VD,MAX VDGR VGS IDM EAS ID ID VCC,MAX VFB PD Derating TA TSTG	650 650 ±30 20 230 5.0 3.5 30 -0.3 to VSD 140 1.11 -25 to +85 -55 to +150	V V V ADC MJ ADC ADC V V V V V C C C C C C C C C C C C C C
Gate-source (GND) voltage Drain current pulsed ⁽²⁾ Single pulsed avalanche energy ⁽³⁾ Continuous drain current (T _C =25°C) Continuous drain current (T _C =100°C) Maximum Supply voltage Input voltage range Total power dissipation Operating ambient temperature	VGS IDM EAS ID ID VCC,MAX VFB PD Derating TA	±30 20 230 5.0 3.5 30 -0.3 to VSD 140 1.11 -25 to +85	V ADC MJ ADC ADC V V V W W CC CC
Drain current pulsed ⁽²⁾ Single pulsed avalanche energy ⁽³⁾ Continuous drain current (T _C =25°C) Continuous drain current (T _C =100°C) Maximum Supply voltage Input voltage range Total power dissipation Operating ambient temperature	IDM EAS ID ID VCC,MAX VFB PD Derating TA	20 230 5.0 3.5 30 -0.3 to VSD 140 1.11 -25 to +85	ADC MJ ADC ADC V V W W/°C °C
Single pulsed avalanche energy (3) Continuous drain current (Tc=25°C) Continuous drain current (Tc=100°C) Maximum Supply voltage Input voltage range Total power dissipation Operating ambient temperature	EAS ID ID VCC,MAX VFB PD Derating TA	230 5.0 3.5 30 -0.3 to VSD 140 1.11 -25 to +85	mJ ADC ADC V V W W/°C °C
Continuous drain current (T _C =25°C) Continuous drain current (T _C =100°C) Maximum Supply voltage Input voltage range Total power dissipation Operating ambient temperature	ID ID VCC,MAX VFB PD Derating TA	5.0 3.5 30 -0.3 to VSD 140 1.11 -25 to +85	ADC ADC V V W W/°C °C
Continuous drain current (Tc=100°C) Maximum Supply voltage Input voltage range Total power dissipation Operating ambient temperature	VCC,MAX VFB PD Derating TA	3.5 30 -0.3 to VSD 140 1.11 -25 to +85	ADC V V W W V ° C ° C
Maximum Supply voltage Input voltage range Total power dissipation Operating ambient temperature	VCC,MAX VFB PD Derating TA	30 -0.3 to VSD 140 1.11 -25 to +85	V V W W/°C
Input voltage range Total power dissipation Operating ambient temperature	VFB PD Derating TA	-0.3 to V _{SD} 140 1.11 -25 to +85	V W/°C °C
Total power dissipation Operating ambient temperature	P _D Derating T _A	140 1.11 -25 to +85	W W/°C
Operating ambient temperature	Derating T _A	1.11 -25 to +85	\/\(\frac{\circ}{\circ}\)
Operating ambient temperature	TA	-25 to +85	O°C
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Notes: 1. Tj=25°C to 150°C 2. Repetitive rating: Pulse width limited by maximul 3. L=30mH, VDD=50V, RG= 27Ω, starting Tj=25°C	TSTG	-55 to + 50	Remi or
Notes: 1. Tj=25°C to 150°C 2. Repetitive rating: Pulse width limited by maximul 3. L=30mH, VDD=50V, RG= 27Ω, starting Tj=25°C	im junction temperatu	NDED FOR	semi or
S DEVICE PLEASER	ONTACI	FOR"	

Electrical Characteristics (SFET part)

(Ta=25°C unless otherwise specified)

	Symbol	Condition	Min.	Тур.	Max.	Uni
Drain source breakdown voltage	BVDSS	VGS=0V, ID=50μA	650	-	-	V
Zero gate voltage drain current	IDSS	VDS=Max., Rating, VGS=0V	-	-	50	μΑ
Zero gate voltage drain current	פפטי	V _{DS} =0.8Max., Rating, V _{GS} =0V, T _C =125°C	-	-	200	μΑ
Static drain source on resistance (note)	RDS(ON)	Vgs=10V, ID=2.5A	-	1.76	2.2	Ω
Forward transconductance (note)	gfs	V _{DS} =50V, I _D =2.5A	2.5		-	S
Input capacitance	Ciss	.,,	-	1457	-	,
Output capacitance	Coss	VGS=0V, VDS=25V, f=1MHz	-	130	7 - ,	95
Reverse transfer capacitance	Crss	1-11VII 12	-	38.8		
Turn on delay time	td(on)	V _{DD} =0.5BV _{DSS} , I _D =5.0A	-	1	60	
Rise time	tr	(MOSFET switching		TE	150	_
Turn off delay time	td(off)	time are essentially independent of	0	-	300	nS
Fall time	tf	operating temperature)	77	in	130	
Total gate charge	Qg	VGS=10V, ID=5.0A, VDS=0.5BVDSS (MOSFET	-6	34.7	56	
(gate-source+gate-drain) Gate source charge	Qgs	switching time are	9	10.3	-	nC
(gate-source+gate-drain)	Qgs	switching time are essentially independent of	0/2	10.3 22.3	-	nC

Electrical Characteristics (CONTROL part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit		
UVLO SECTION				•	•	•		
Start threshold voltage	VSTART	-	14	15	16	V		
Stop threshold voltage	VSTOP	After turn on	9	10	11	V		
OSCILLATOR SECTION				•	•	•		
Initial accuracy	Fosc	KA1M0565R	61	67	73	- kHz		
Initial accuracy		KA1H0565R	90	100	110			
Frequency change with temperature (2)	ΔF/ΔΤ	–25°C ≤ Ta ≤ +85°C	-	±5	±10	%		
Maximum duty avala	D	KA1M0565R	74	77	30	. 60		
Maximum duty cycle	Dmax	KA1H0565R	64	67	70	%		
FEEDBACK SECTION								
Feedback source current	IFB	Ta=25°C, 0V ≤ Vfb ≤ 3V	0.7	0.9	1.1	mA		
Shutdown Feedback voltage	VsD		6.9	7.5	8.1	V		
Shutdown delay current	Idelay	Ta=25°C, 5V ≤ Vfb ≤ VsD	4.0	5.0	6.0	μΑ		
REFERENCE SECTION								
Output voltage ⁽¹⁾	Vref	Ta=25°C	4.80	5.00	5.20	V		
Temperature Stability (1)(2)	Vref/△T	-25°C ≤ Ta ≤ +85°C	0,,	0.3	0.6	mV/°C		
CURRENT LIMIT (SELF-PROTECTION	SECTION	SALIK	2	14.	•	•		
Peak Current Limit	lover	Max inductor current	3.03	3.5	3.92	Α		
PROTECTION SECTION		Mr. L.						
Thermal shutdown temperature (Tj) (1)	TSD	10 -2 "	140	160	-	°C		
Over voltage protection voltage	VOVP	(K) 50,	23	25	28	V		
TOTAL DEVICE SECTION				•	•	•		
Start Up current	START	VCC=14V	0.1	0.3	0.4	mA		
Operating supply current (control part only)	lor	Ta=25°C	6	12	18	mA		
VCC zener voltage	Vz	ICC=20mA	30	32.5	35	V		

Note:

^{1.} These parameters, although quaranteed, are not 100% tested in production

^{2.} These parameters, although guaranteed, are tested in EDS (wafer test) process

Typical Performance Characteristics

(These characteristic graphs are normalized at Ta=25°C)

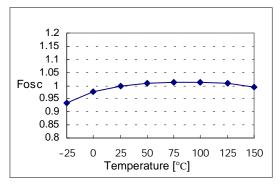


Figure 1. Operating Frequency

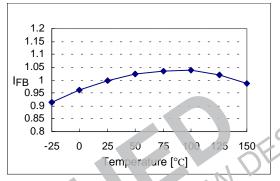


Figure 2. Feedback Source Current

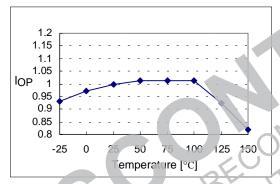


Figure 3. Operating Supply Current

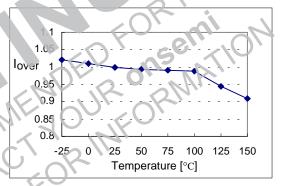


Figure 4. Peak Current Limit

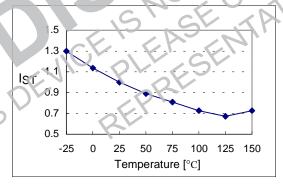


Figure 5. Start up Current

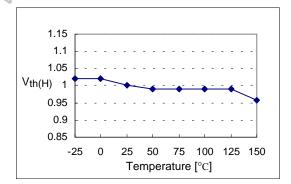


Figure 6. Start Threshold Voltage

Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at Ta=25°C)

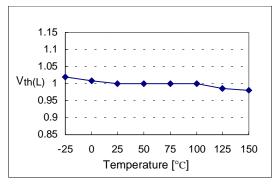


Figure 7. Stop Threshold Voltage

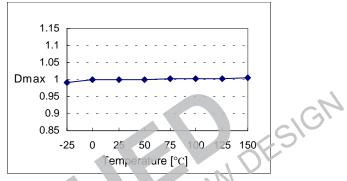


Figure 8. Maximum Duty Cycle

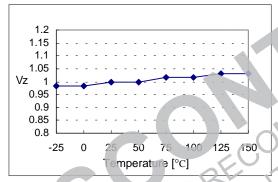


Figure 9. Vcc Zener Voltage

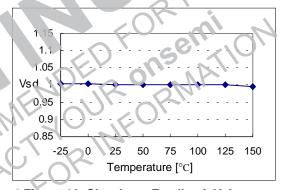


Figure 10. Shutdown Feedback Voltage

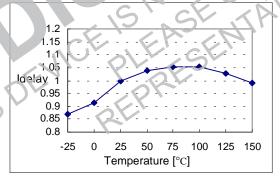


Figure 11. Shutdown Delay Current

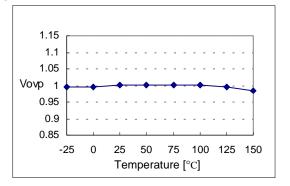


Figure 12. Over Voltage Protection

Typical Performance Characteristics (Continued)

(These characteristic grahps are normalized at Ta=25°C)

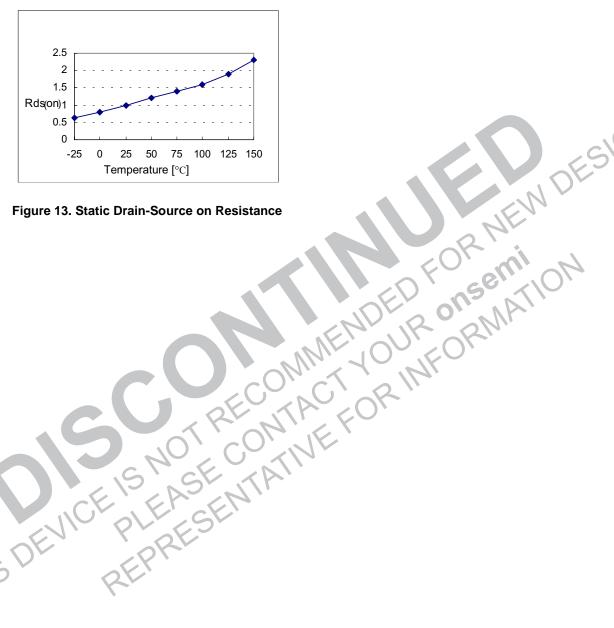
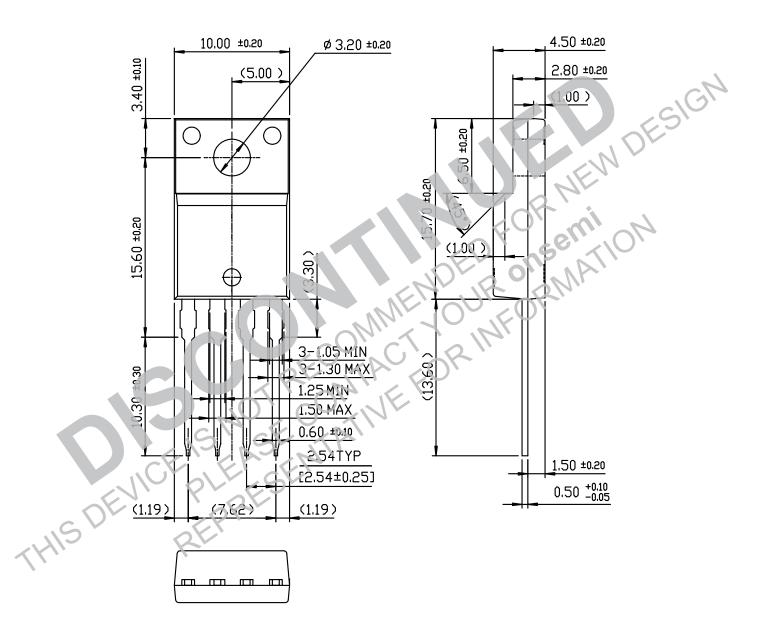


Figure 13. Static Drain-Source on Resistance

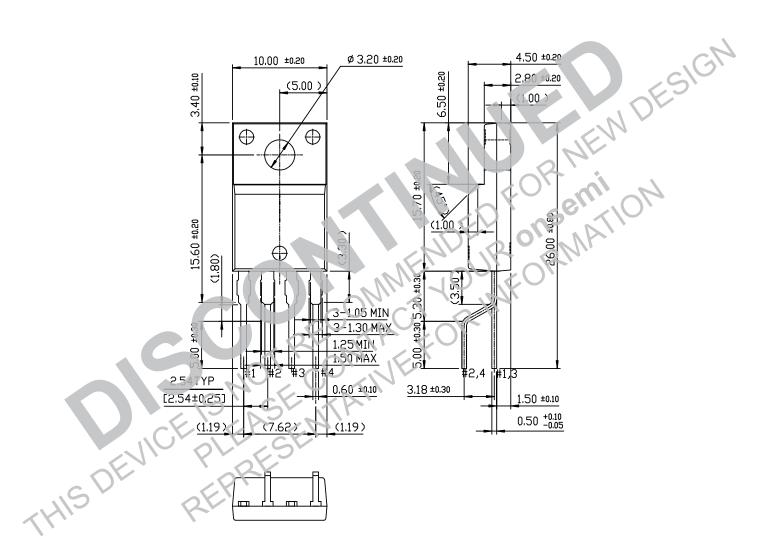
Package Dimensions

TO-220F-4L



Package Dimensions (Continued)

TO-220F-4L(Forming)



Ordering Information

Product Number	Package	Rating	Fosc
KA1M0565R-TU	TO-220F-4L	650V, 5A	67kHz
KA1M0565R-YDTU	TO-220F-4L(Forming)	030 V, 3A	O/ KI IZ
KA1H0565R-TU	TO-220F-4L	650V, 5A	100kHz
KA1H0565R-YDTU	TO-220F-4L(Forming)	030 V, 3A	TOURHZ

TU: Non Forming Type YDTU: Forming Type



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